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**Inclosure Material:**

Metal all semiconductor device diode

**Overall Length:**

1.330 inches all transistor

**Mounting Facility Quantity:**

1 all transistor

**Internal Configuration:**

Junction contact all transistor

**Internal Junction Configuration:**

Npn all transistor

**Component Function Relationship:**

Matched

**Component Name And Quantity:**

4 transistor

**Mounting Method:**

Threaded stud all transistor

**Overall Width Across Flats:**

0.667 inches all transistor and 0.687 inches all transistor

**Thread Size:**

0.250 inches all transistor

**Semiconductor Material:**

Silicon all transistor

**Voltage Rating In Volts Per Characteristic:**

300.0 breakdown voltage, collector-to-emitter, with base short-circuited to emitter all transistor and 250.0 breakdown voltage, collector-to-emitter, base open all transistor and 7.0 breakdown voltage, emitter to collector, base open all transistor

**Current Rating Per Characteristic:**

10.00 amperes source cutoff current all transistor

**Power Rating Per Characteristic:**

75.0 watts small-signal input power, common-collector preset all transistor

**Precious Material And Location:**

Terminal surface gold

**Precious Material:**

Gold

**Terminal Type And Quantity:**

3 tab, solder lug all transistor

**Shelf Life:**

N/a

**Unit Of Measure:**

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**Demilitarization:**

No

**Fiig:**

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